HITACHI

2SC4964

Silicon NPN Bipolar Transistor

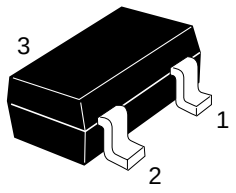
Application

VHF & UHF wide band amplifire

Features

- Low Ron and high performance for RF switch.
- Capable of high density mounting.

MPAK



1. Emitter
2. Base
3. Collector

Table 1 Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	12	V
Collector to emitter voltage	V_{CEO}	8	V
Emitter to base voltage	V_{EBO}	3	V
Collector current	I_C	100	mA
Collector power dissipation	P_C	150	mW
Junction temperature	T_j	150	°C
Storage temperature	Tstg	–55 to +150	°C

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Table 2 Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	12	—	—	V	I_C = 10 µA I_E = 0
Collector cutoff current	I_{CBO}	—	—	1	µA	V_{CB} = 10 V, I_E = 0
	I_{CEO}	—	—	1	mA	V_{CE} = 8 V, R_{BE} = ∞
Emitter cutoff current	I_{EBO}	—	—	10	µA	V_{EB} = 3 V, I_C = 0
DC current transfer ratio	h_{FE}	100	250	600		V_{CE} = 5 V, I_C = 5 mA
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	200	300	mV	I_C = 80mA I_B = 5mA
Output capacitance	Cob	—	1.2	1.6	pF	V_{CB} = 5 V, I_E = 0, f = 1 MHz
On resistance	Ron	—	2.0	—	Ω	I_B = 2.5 mA f = 1 kHz

Note: Marking of 2SC4964 is "YV–".